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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent of : Attn: Certificate of
Tetsuya MATSUTANI : Correction Branch
Patent No. 7,316,972 : Atty Docket No. 2003_1039A
Issued January 8, 2008 :
Confirmation No. 7670
CONTACT HOLE FORMATION METHOD

Certificate
FEB 15 2008
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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ACCOUNT NO. 23-0975

Sir:

In accordance with the provisions of 37 CFR 1.322, it is respectfully requested that a Certificate of Correction issue to correct the following:

In claim 13, column 12, lines 22-52, claim 13 should read as follows,

--A method for forming a semiconductor device comprising:

forming a first group of interconnections on a first region of a substrate so that the first group of interconnections are densely arranged;

forming a second group of interconnections on a second region of the substrate so that the second group of interconnections are sparsely arranged;

forming a first dielectric film on the substrate;

planarizing the first dielectric film;

forming a second dielectric film on the first dielectric film, the second dielectric film having an etching rate different from an etching rate of the first dielectric film; and then

forming contact holes to a uniform depth through the first dielectric film and the second dielectric film,

wherein an entire surface of the first dielectric film is continuous and higher than a top surface of the interconnections just prior to planarizing the first dielectric film, and

wherein planarizing the first dielectric film results in the first dielectric film having a uniform thickness at those portions through which said contact holes are formed.--

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In claim 9, column 12, line 10, "pf" should be --of--.

In claim 29, column 13, line 50, "than the the etching" should be --than the etching--.

In claim 36, column 14, line 28, "notride" should be --nitride--.

In claim 57, column 16, line 4, "difernt" should be --different--.

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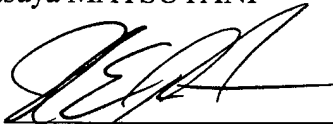
REMARKS

Each of the errors listed above apparently arose due to PTO mistakes. Accordingly, a Certificate of Correction should issue at no expense to patentee. Form PTO-1050 accompanies this request.

Respectfully submitted,

Tetsuya MATSUTANI

By



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February 13, 2008

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To: The Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

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CERTIFICATE OF CORRECTION**

PATENT NO : 7,316,972
DATED : January 8, 2008
INVENTOR(S) : Tetsuya MATSUTANI

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wherein planarizing the first dielectric film results in the first dielectric film having a uniform thickness at those portions through which said contact holes are formed.--.

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